

Ti-Ta ALLOY SPUTTERING TARGET AND PRODUCTION METHOD THEREFOR

ABSTRACT

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A Ti-Ta alloy sputtering target containing 0.1 to 30 at% of Ta, and remainder being Ti and unavoidable impurities, wherein the Ti-Ta alloy sputtering target has an oxygen content of 400 wtpm or less. The present invention has a favorable surface texture with a low oxygen content and is readily processable due to its low hardness, and therefore the

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present invention yields a superior effect of being able to suppress the generation of particles during sputtering.

Fig. 1